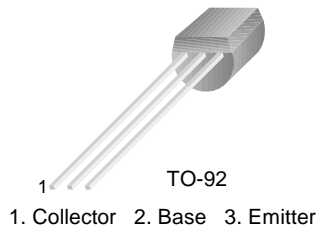


BC327A

PNP Epitaxial Silicon Transistor

Switching and Amplifier Applications

- Suitable for AF-Driver stages and low power output stages



Absolute Maximum Ratings * $T_a = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|-----------------------------|-----------|------------------|
| V_{CES} | Collector-Emitter Voltage | -60 | V |
| V_{CEO} | Collector-Emitter Voltage | -60 | V |
| V_{EBO} | Emitter-Base Voltage | -5 | V |
| I_C | Collector Current (DC) | -800 | mA |
| P_C | Collector Power Dissipation | 625 | mW |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | -55 ~ 150 | $^\circ\text{C}$ |

Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|------------------------|--------------------------------------|--|-----------|------|------|-------|
| BV_{CEO} | Collector-Emitter Breakdown Voltage | $I_C = -10\text{mA}, I_B = 0$ | -60 | | | V |
| BV_{CES} | Collector-Emitter Breakdown Voltage | $I_C = -100\mu\text{A}, V_{BE} = 0$ | -60 | | | V |
| BV_{EBO} | Emitter-Base Breakdown Voltage | $I_E = -100\mu\text{A}, I_C = 0$ | -5 | | | V |
| I_{CES} | Collector Cut-off Current | $V_{CE} = -45\text{V}, V_{BE} = 0$ | | | -100 | nA |
| h_{FE1} h_{FE2} | DC Current Gain | $V_{CE} = -1\text{V}, I_C = -100\text{mA}$ $V_{CE} = -1\text{V}, I_C = -500\text{mA}$ | 100 40 | | 400 | |
| $V_{CE}(\text{sat})$ | Collector-Emitter Saturation Voltage | $I_C = -500\text{mA}, I_B = -50\text{mA}$ | | | -0.7 | V |
| $V_{BE}(\text{on})$ | Base-Emitter On Voltage | $V_{CE} = -1\text{V}, I_C = -300\text{mA}$ | | | -1.2 | V |
| f_T | Current Gain Bandwidth Product | $V_{CE} = -5\text{V}, I_C = -10\text{mA}, f = 20\text{MHz}$ | | 100 | | MHz |
| C_{ob} | Output Capacitance | $V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$ | | 12 | | pF |

Typical Performance Characteristics

Figure 1. Static Characteristic

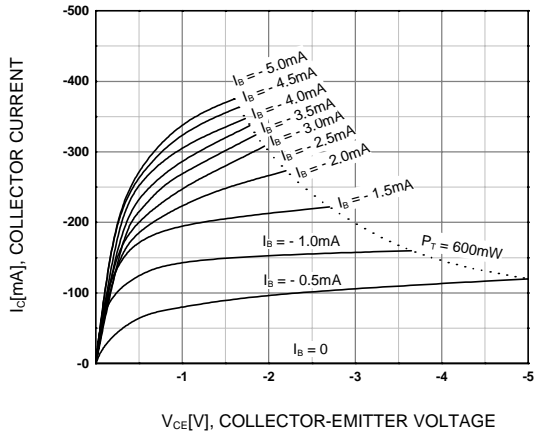


Figure 2. Static Characteristic

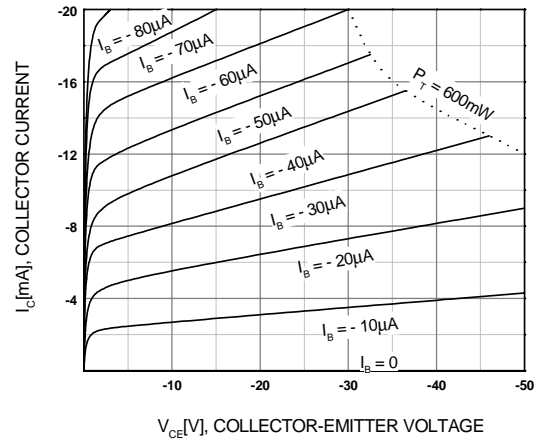
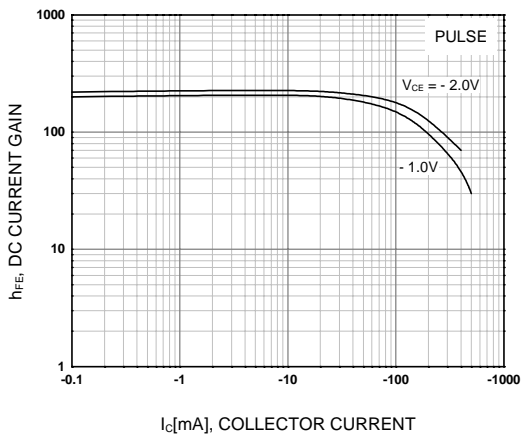


Figure 3. DC Current Gain



**Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**

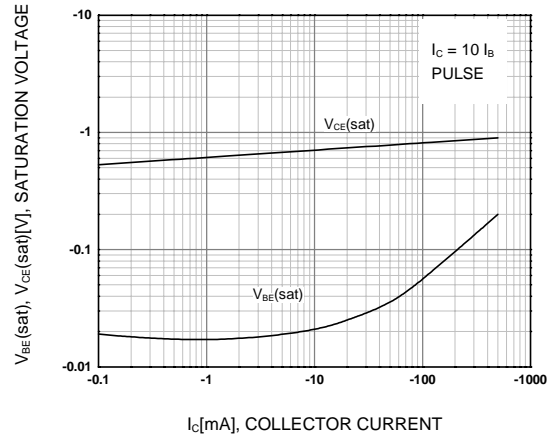


Figure 5. Base-Emitter On Voltage

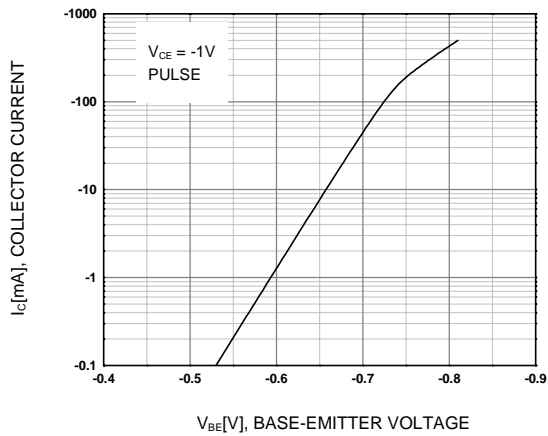
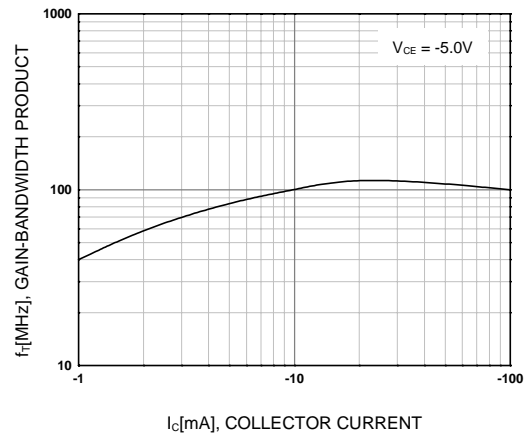
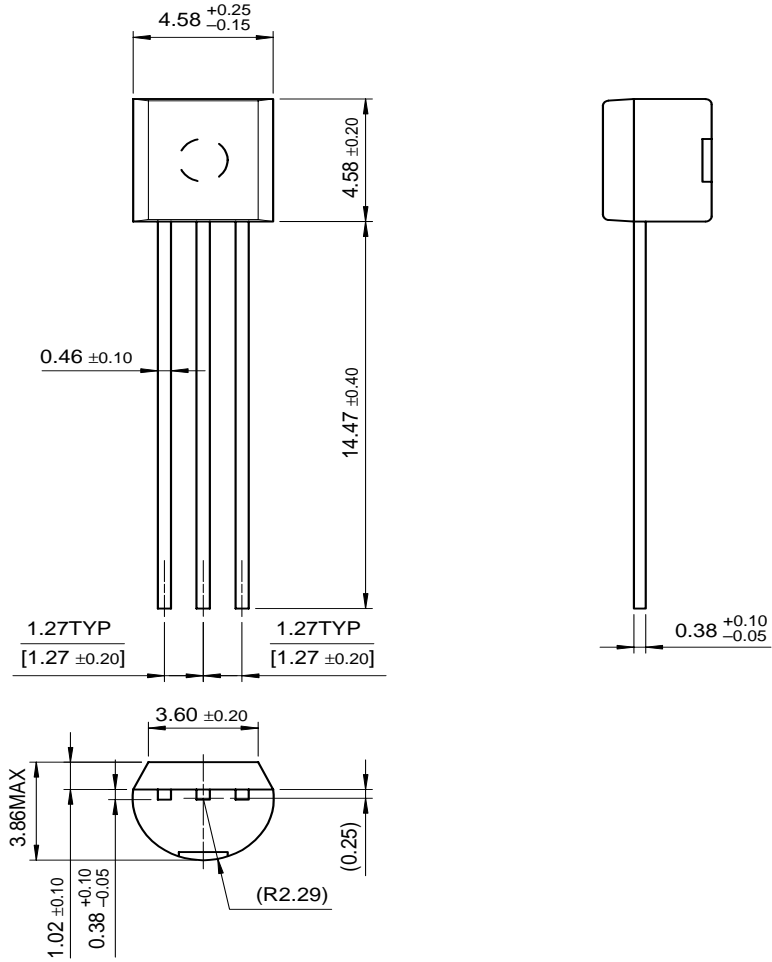


Figure 6. Gain Bandwidth Product



Mechanical Dimensions

TO-92



Dimensions in Millimeters

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